



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
PNP Switching Transistor**

VOLTAGE 40 Volts CURRENT 0.2 Ampere

CH3906TPT

APPLICATION

- * Telephony and professional communication equipment.
- * Other switching applications.

FEATURE

- * Small surface mounting type. (SC-75/SOT-416)
- * Low current (Max.=200mA).
- * Suitable for high packing density.
- * Low voltage (Max.=40V).
- * High saturation current capability.
- * Voltage controlled small signal switch.

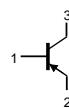
CONSTRUCTION

- * PNP Switching Transistor

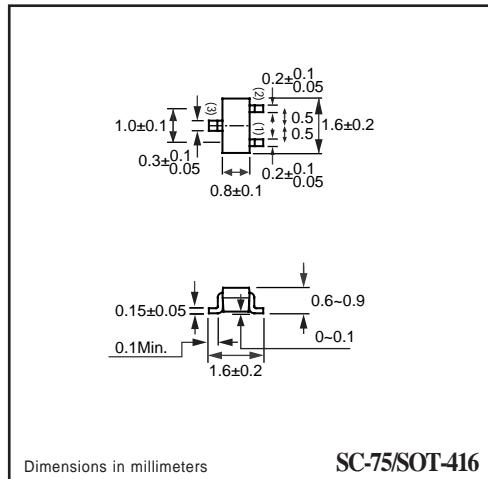
MARKING

- * C

CIRCUIT



SC-75/SOT-416



SC-75/SOT-416

Dimensions in millimeters

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	-40	V
V_{CEO}	collector-emitter voltage	open base	—	-40	V
V_{EBO}	emitter-base voltage	open collector	—	-5	V
I_C	collector current DC		—	-200	mA
I_{CM}	peak collector current		—	-200	mA
I_{BM}	peak base current		—	-100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1	—	150	mW
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CH3906TPT)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

- Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25^\circ C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30 V$	—	-50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 6 V$	—	-50	nA
h_{FE}	DC current gain	$V_{CE} = -1 V$; note 1 $I_C = -0.1 mA$ $I_C = -1 mA$ $I_C = -10 mA$ $I_C = -50 mA$ $I_C = -100 mA$	60 80 100 60 30	— — 300 — —	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10 mA; I_B = -1 mA$ $I_C = -50 mA; I_B = -5 mA$	— —	-250 -400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10 mA; I_B = -1 mA$ $I_C = -50 mA; I_B = -5 mA$	-650 —	-850 -950	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -5 V; f = 1 MHz$	—	4.5	pF
C_e	emitter capacitance	$I_C = i_e = 0; V_{EB} = -500 mV; f = 1 MHz$	—	10	pF
f_T	transition frequency	$I_C = 10 mA; V_{CE} = -20 V; f = 100 MHz$	250	—	MHz
F	noise figure	$I_C = 100 \mu A; V_{CE} = -5 V; R_S = 1 k\Omega; f = 10 Hz to 15.7 kHz$	—	4	dB

Switching times (between 10% and 90% levels);

t_{on}	turn-on time	$I_{Con} = -10 mA; I_{Bon} = -1 mA; I_{Boff} = 1 mA$	—	65	ns
t_d	delay time		—	35	ns
t_r	rise time		—	35	ns
t_{off}	turn-off time		—	300	ns
t_s	storage time		—	225	ns
t_f	fall time		—	75	ns

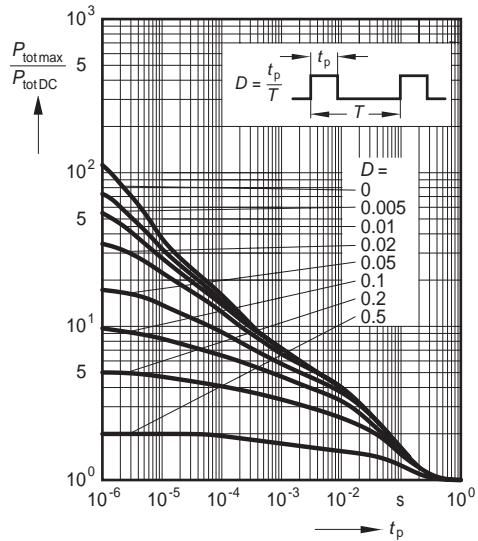
Note

- Pulse test: $t_p \leq 300 \mu s; \delta \leq 0.02$.

RATING CHARACTERISTIC CURVES (CH3906TPT)

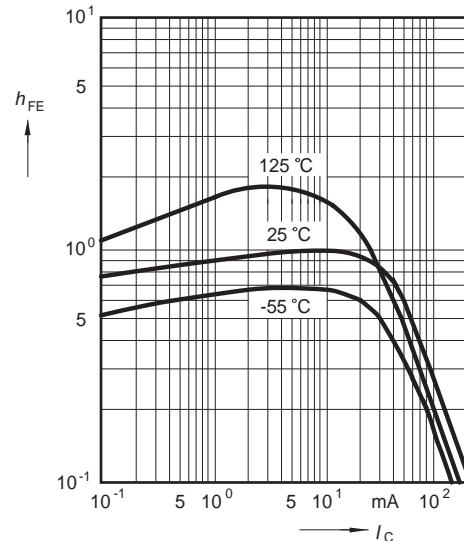
Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$



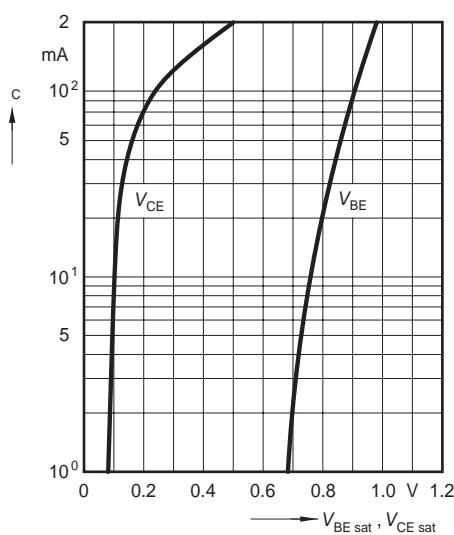
DC current gain $h_{\text{FE}} = f(I_C)$

$$V_{\text{CE}} = 1 \text{ V, normalized}$$



Saturation voltage $I_C = f(V_{\text{BEsat}}, V_{\text{CESat}})$

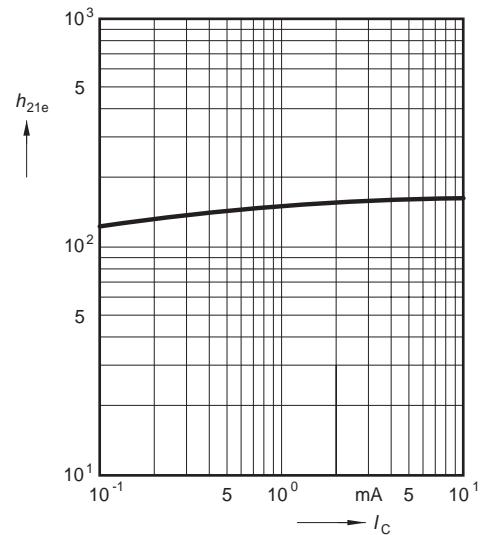
$$h_{\text{FE}} = 10$$



Short-circuit forward current

$$\text{transfer ratio } h_{21e} = f(I_C)$$

$$V_{\text{CE}} = 10 \text{ V, } f = 1 \text{ MHz}$$

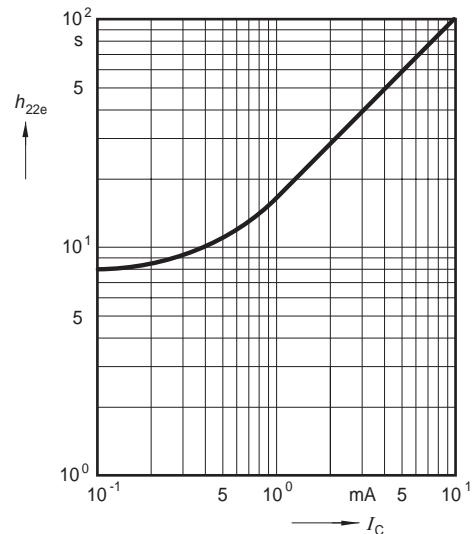


RATING CHARACTERISTIC CURVES (CH3906TPT)

Open-circuit output admittance

$$h_{22e} = f(I_C)$$

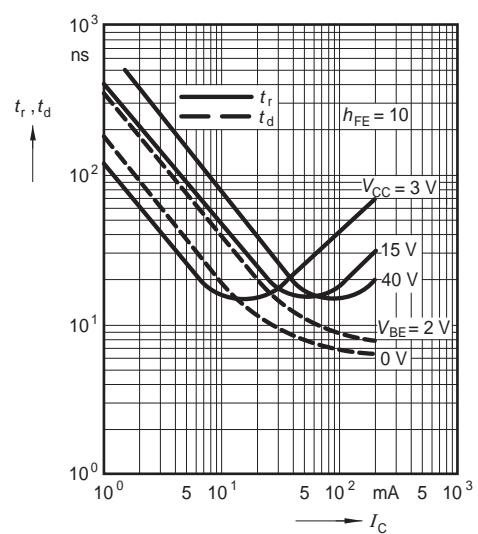
$V_{CE} = 10V, f = 1MHz$



Fall time $t_f = f(I_C)$

Delay time $t_d = f(I_C)$

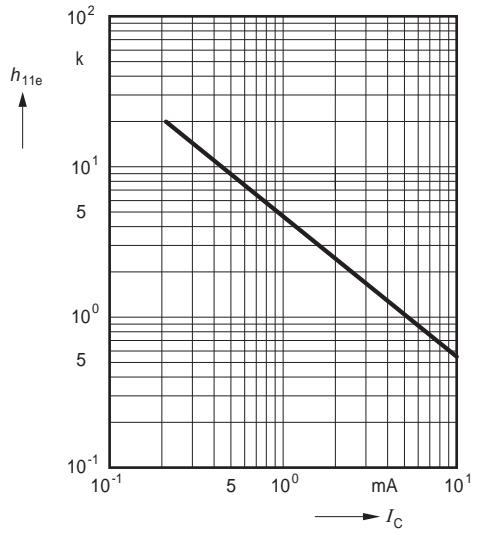
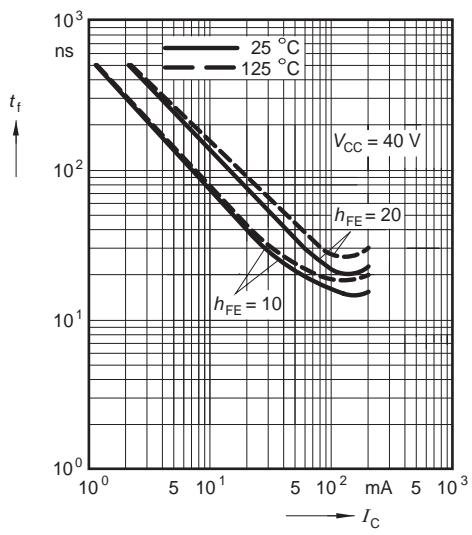
Rise time $t_r = f(I_C)$



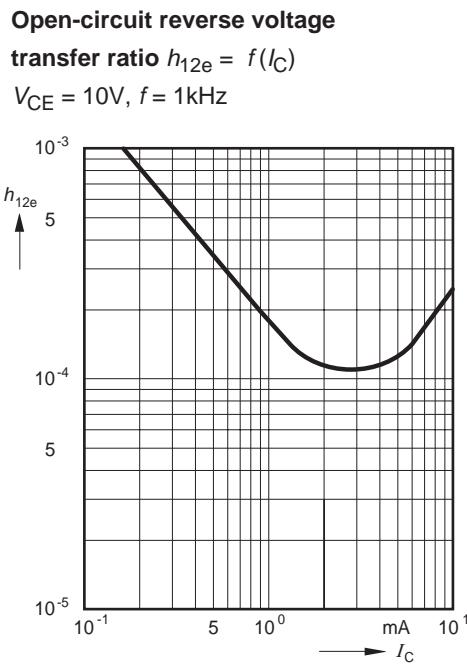
Input impedance

$$h_{11e} = f(I_C)$$

$V_{CE} = 10 V, f = 1kHz$



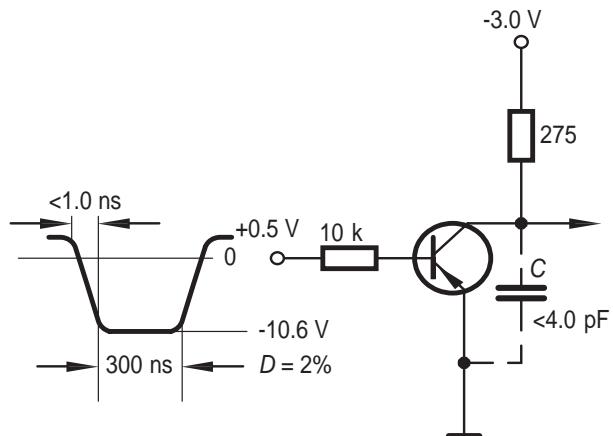
RATING CHARACTERISTIC CURVES (CH3906TPT)



RATING CHARACTERISTIC CURVES (CH3906TPT)

Test circuit

Delay and rise time



Storage and fall time

